

CBR1U-D010
CBR1U-D020

1 AMP ULTRA FAST
SILICON BRIDGE RECTIFIER

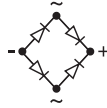
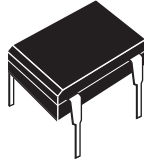


www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBR1U-D010, CBR1U-D020 types are silicon full wave ultra fast bridge rectifiers mounted in a durable epoxy molded case, utilizing glass passivated chips.

MARKING: FULL PART NUMBER



DIP CASE

MAXIMUM RATINGS:

($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	CBR1U-D010	CBR1U-D020	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	V
DC Blocking Voltage	V_R	100	200	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	V
Average Forward Current ($T_A=40^\circ\text{C}$)	I_O		1.0	A
Peak Forward Surge Current	I_{FSM}		50	A
Operating and Storage				
Junction Temperature	T_J, T_{stg}	-65 to +150		$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	40		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

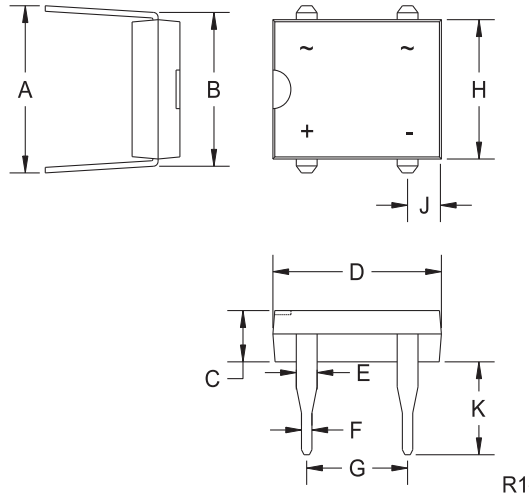
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=\text{Rated } V_{RRM}$		5.0	μA
I_R	$V_R=\text{Rated } V_{RRM}, T_A=125^\circ\text{C}$		1.0	mA
V_F	$I_F=1.0\text{A}$		1.05	V
t_{rr}	$I_F=500\text{mA}, I_R=1.0\text{A}, I_{rr}=250\text{mA}$		50	ns

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DIP CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.300	0.350	7.62	8.89
B	0.285	0.315	7.24	8.00
C	0.086	0.098	2.18	2.49
D	0.316	0.335	8.03	8.51
E	0.035	0.045	0.89	1.14
F	0.018	0.022	0.46	0.56
G	0.195	0.205	4.95	5.21
H	0.245	0.255	6.22	6.48
J	0.055	0.075	1.40	1.91
K	0.150	0.185	3.81	4.70

DIP (REV: R1)

MARKING: FULL PART NUMBER

R0 (28-February 2011)